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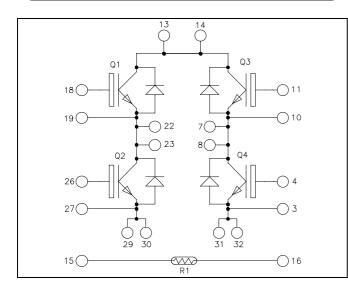
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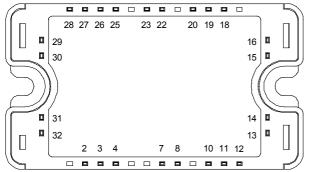
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Full - Bridge Fast Trench + Field Stop IGBT3 Power Module





All multiple inputs and outputs must be shorted together Example: 13/14 ; 29/30 ; 22/23 ...

Absolute maximum ratings

APTGT50H120T3G

$V_{CES} = 1200V$ $I_C = 50A$ @ Tc = 80°C

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fast Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- Easy paralleling due to positive T_C of V_{CEsat}
- Each leg can be easily paralleled to achieve a phase leg of twice the current capability
- RoHS Compliant

Symbol	Parameter		Max ratings	Unit
V _{CES}	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_C = 25^{\circ}C$	75	
I _C	Continuous Conector Current	$T_C = 80^{\circ}C$	50	А
I _{CM}	Pulsed Collector Current	$T_C = 25^{\circ}C$	100	
V _{GE}	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_C = 25^{\circ}C$	270	W
RBSOA	Reverse Bias Safe Operating Area	$T_J = 125^{\circ}C$	100A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

www.microsemi.com



All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Т	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ $T_j = 25^{\circ}C$				250	μA
I _{CES}		$V_{CE} = 1200V$	$T_{j} = 125^{\circ}C$			500	μЛ
V	Collector Emitter saturation Voltage	$\begin{array}{c} V_{GE} = 15V & T_{j} = 25^{\circ}C \\ I_{C} = 50A & T_{j} = 125^{\circ}C \end{array}$	$T_j = 25^{\circ}C$	1.4	1.7	2.1	V
V _{CE(sat)}			$T_{j} = 125^{\circ}C$		2.0		v
V _{GE(th)}	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		5.0	5.8	6.5	V
I _{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$			3600		pF
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz			160		pr
T _{d(on)}	Turn-on Delay Time		Inductive Switching (25°C)		90		
T _r	Rise Time	$V_{GE} = \pm 15V$			30		
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 50A$			420		ns
T _f	Fall Time	$R_G = 18\Omega$		70			
T _{d(on)}	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$ $R_G = 18\Omega$			90		
Tr	Rise Time				50		
T _{d(off)}	Turn-off Delay Time				520		ns
$T_{\rm f}$	Fall Time				90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 50A$ $R_G = 18\Omega$	$T_j = 125^{\circ}C$		5		m I
E _{off}	Turn-off Switching Energy		$T_j = 125^{\circ}C$		5.5		mJ

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I _{RM}	Mariana Darana Lasha a Comut	V _R =1200V	$T_j = 25^{\circ}C$			250	۸
IRM	Maximum Reverse Leakage Current	v _R -1200 v	$T_{j} = 125^{\circ}C$			500	μA
$I_{\rm F}$	DC Forward Current		$Tc = 70^{\circ}C$		60		А
		$I_F = 60A$			2	2.5	
V _F	Diode Forward Voltage	$I_F = 120A$			2.3		V
		$I_F = 60A$	$T_{j} = 125^{\circ}C$		1.8		
t _{rr}	Reverse Recovery Time	$I_{\rm r} = 60A$	$T_j = 25^{\circ}C$		400		ns
٩ſſ			$T_{j} = 125^{\circ}C$		470		115
0	Reverse Recovery Charge $di/dt = 200 A/\mu s$		$T_j = 25^{\circ}C$		1200		nC
Q _{rr}				$T_{j} = 125^{\circ}C$		4000	
Er	Reverse Recovery Energy	$I_F = 60A$ $V_R = 800V$ $di/dt = 1000A/\mu s$	$T_j = 125^{\circ}C$		2.2		mJ

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Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Тур	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K
	<i>D</i>				

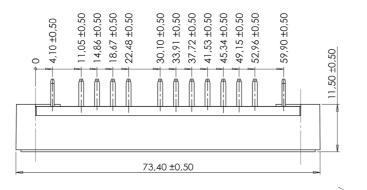
$$R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$
 T: Thermis
R_T: Therm

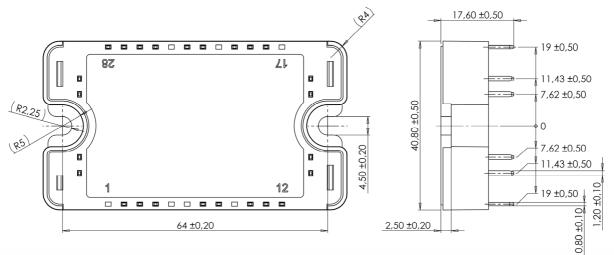
Thermistor temperature T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance		IGBT			0.45	°C/W
R _{th} JC		Diode			0.9	C/W	
VISOL	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
TJ	Operating junction temperature range	Operating junction temperature range				150	
T _{STG}	Storage Temperature Range		-40		125	°C	
T _C	Operating Case Temperature					100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					110	g

SP3 Package outline (dimensions in mm)





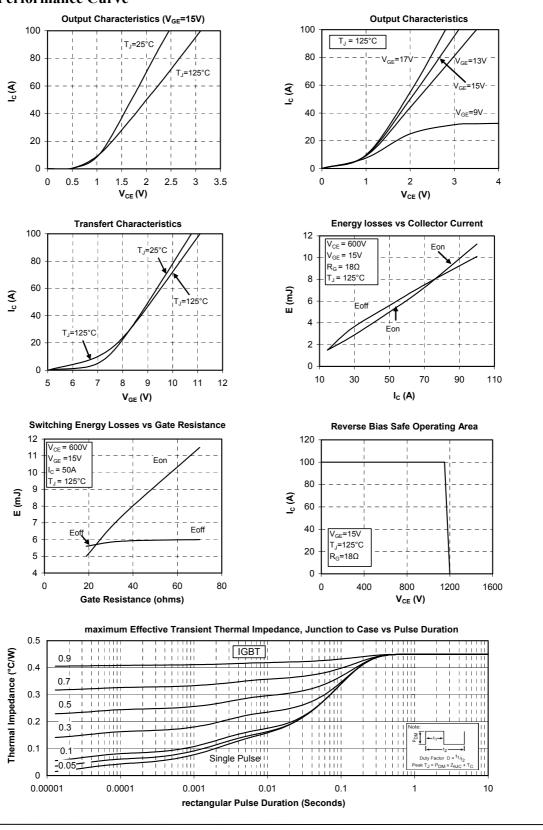
See application note 1901 - Mounting Instructions for SP3 Power Modules on www.microsemi.com

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Typical Performance Curve

APTGT50H120T3G



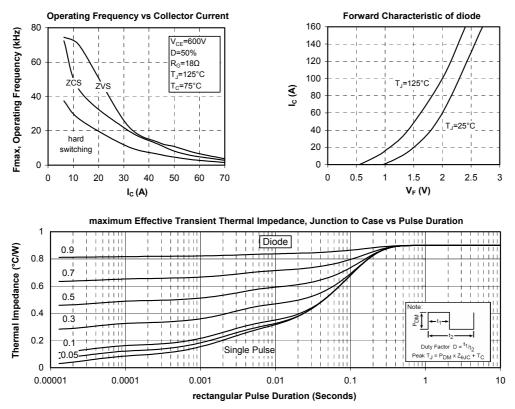
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APTGT50H120T3G

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